UTC UNISONIC TECHNOLOGIES CO., LTD

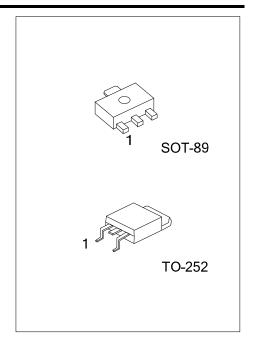
UN1066

NPN SILICON TRANSISTOR

HIGH SPEED SWITCHING TRANSISTOR

FEATURES

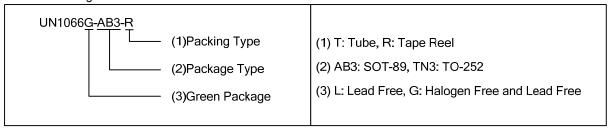
- * Low $V_{\text{CE}(\text{SAT})}$ voltage, up to 3A
- * Suitable for fast switching applications
- * High current gain



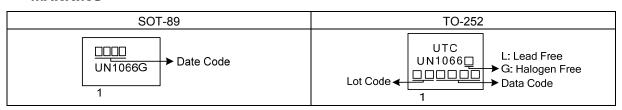
ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
-	UN1066G-AB3-R	SOT-89	В	С	Е	Tape Reel	
UN1066L-TN3-R	UN1066G-TN3-R	TO-252	В	С	Е	Tape Reel	

Pin Assignment: B: Base C: Collector E: Emitter Note:



MARKING



www.unisonic.com.tw 1 of 5

■ **ABSOLUTE MAXIMUM RATING** (T_A=25°C, unless otherwise specified)

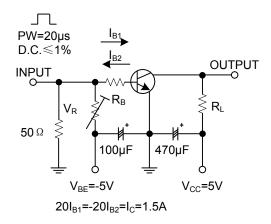
PARAMETER	SYMBOL	RATINGS	UNIT
Collector to Base Voltage	BV_CBO	20	V
Collector to Emitter Voltage	BV _{CEO}	15	V
Emitter to Base Voltage	BV_{EBO}	5	V
Collector Current	Ic	6	Α
Collector Current (Pulse)	I _{CP}	9	Α
Base Current	l _B	600	mA
Collector Dissipation (T _C =25°C)	Pc	3.5	W
Junction Temperature	T_J	150	°C
Storage Temperature	T _{STG}	-55 ~ + 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

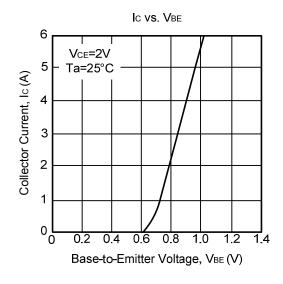
■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

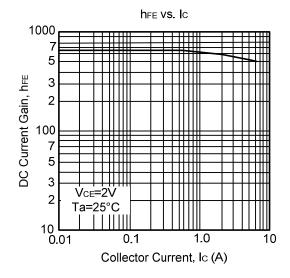
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector to Base Breakdown Voltage	BV _{CBO}	I _C =10μA, I _E =0	20			V
Collector to Emitter Breakdown Voltage	BV _{CEO}	I _C =1mA, R _{BE} =∞	15			V
Emitter to Base Breakdown Voltage	BV_{EBO}	I _E =10μA, I _C =0	5			V
Collector-to-Emitter Saturation Voltage	VCE(SAT)	I _C =1.5A, I _B =30mA			180	mV
		I _C =3A, I _B =60mA			300	mV
Base-to-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =1.5A, I _B =30mA			1.2	V
Collector Cutoff Current	I _{CBO}	V _{CB} =12V, I _E =0			0.1	μΑ
Emitter Cutoff Current	I _{EBO}	V _{EB} =4V, I _C =0			0.1	μΑ
DC Current Gain	h _{FE}	V_{CE} =0.5V, I_{C} =5A	250			
Gain-Bandwidth Product	f _T	V _{CE} =2V, I _C =500mA	100			MHz
Output Capacitance	C _{ob}	V _{CB} =10V, f=1MHz			50	pF
Turn-on Time	ton	Refer to Test Circuit			50	ns
Storage Time	t _{stg}	Refer to Test Circuit			250	ns
Fall Time	t _F	Refer to Test Circuit			25	ns

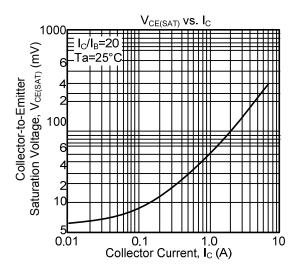
■ TEST CIRCUIT

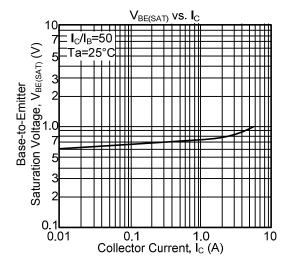


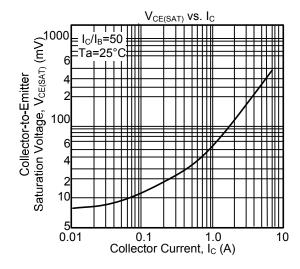
■ TYPICAL CHARACTERISTICS











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